L Number	Hits	Search Text	DB	Time stamp
1	45	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
		medium or film )) and (protection near (film or layer or	EPO; JPO;	
		region or medium)) and ridge and (refractive near (index or	DERWENT;	
	_	indice))	IBM_TDB	
4	2	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
		medium or film )) and (protection near2 dielectric near2 (film	EPO; JPO;	
		or layer or region or medium)) and ridge and (refractive near	DERWENT;	
		(index or indice))	IBM_TDB	
3	14	((semiconductor near laser) and (active near (layer or region	USPAT;	2004/05/25 10:33
		or medium or film )) and (((dielectric or insulat\$5 or	EPO; JPO;	
		protect\$5) near (film or layer or region or medium)) same	DERWENT;	
		substrate same ridge same (refractive near (index or indice)))	IBM_TDB	
,	n=	and width) and 257/\$	LICDAT.	2004 (05 (25 10.20
2	25	((semiconductor near laser) and ((active near (layer or region	USPAT;	2004/05/25 10:39
		or medium or film )) AND (protection near (film or layer or	EPO; JPO;	
		region or medium)) SAME (SUBSTRATE)) and ridge and	DERWENT;	
5	1	(refractive near (index or indice))) and width	IBM_TDB	2004 /05 /25 10:24
5	1	((semiconductor near laser) and ((active near (layer or region or medium or film )) AND (dielectric near2 protection near	USPAT; EPO; JPO;	2004/05/25 10:34
-		(film or layer or region or medium)) SAME (SUBSTRATE))	DERWENT;	
		and ridge and (refractive near (index or indice))) and width	IBM_TDB	
_	34	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:30
	J-1	medium or film )) and (protection near (film or layer or	US-PGPUB;	2004/ 00/ 20 10.50
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))	DERWENT;	
			IBM_TDB	
_	28	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/20 13:54
		or medium or film )) and (protection near (film or layer or	US-PGPUB;	,,
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) ) and width	DERWENT;	
ļ		<i>""</i>	IBM_TDB	
-	12	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 10:37
		or medium or film )) SAME (protection near (film or layer or	US-PGPUB;	, ,
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
			IBM_TDB	
-	21	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 15:02
		or medium or film )) AND (protection near (film or layer or	US-PGPUB;	
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
	4-		IBM_TDB	0004 (05 (05 10 5)
-	17	((semiconductor near laser) and ((active near (layer or region	USPAT;	2004/05/25 10:31
		or medium or film )) AND (protection near (film or layer or	US-PGPUB;	
		region or medium)) SAME (SUBSTRATE)) and ridge and	EPO; JPO;	
		(refractive near (index or indice)) ) and width	DERWENT;	
_	10	((semiconductor near laser) and ((active near (layer or region	IBM_TDB	2002/05/20 14:24
-	10	or medium or film )) SAME (protection near (film or layer or	USPAT;	2002/05/20 14:24
		region or medium)) SAME (SUBSTRATE)) and ridge and	US-PGPUB; EPO; JPO;	
		(refractive near (index or indice)) ) and width	DERWENT;	
		(index of mack of marce)) and width	IBM_TDB	
_	12	(semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/20 16:36
-	14	or medium or film )) AND (protection near (film or layer or	US-PGPUB;	2002/00/20 10:30
		region or medium)) SAME (SUBSTRATE)) and ( width same	EPO; JPO;	
		ridge) and (refractive near (index or indice))	DERWENT;	
		(* overland views (***mon of Marcol)	IBM_TDB	
-	11	((semiconductor near laser) and ((active near (layer or region	USPAT;	2002/05/21 08:26
		or medium or film )) AND (protection near (film or layer or	US-PGPUB;	3552, 55, 21 55.20
		region or medium)) SAME (SUBSTRATE)) and (width same	EPO; JPO;	
		ridge) and (refractive near (index or indice)) ) and 372/\$	DERWENT;	
1		riage) and (remactive near (maex of mate)) ) and 5/2/5	DERWILLIAI.	

-	456	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:56
	ļ:	medium or film )) and ((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) and ridge and	EPO; JPO;	
		(refractive near (index or indice))	DERWENT;	
			IBM_TDB	
-	382	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/21 10:59
	İ	medium or film )) and ((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) and ridge and	EPO; JPO;	
ļ		(refractive near (index or indice)) AND substrate and width	DERWENT;	
			IBM_TDB	
-	0	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:14
		medium or film )) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) same substrat) and	EPO; JPO;	
		ridge and (refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	284	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:18
		medium or film )) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) same substrate) and	EPO; JPO;	
		ridge and (refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	131	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 13:21
		medium or film )) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) same substrate	EPO; JPO;	
		same ridge) and (refractive near (index or indice)) and width	DERWENT;	
			IBM_TDB	
-	29	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/05/22 14:31
		medium or film )) and (((dielectric or insulat\$5 or protect\$5)	US-PGPUB;	
		near (film or layer or region or medium)) same substrate	EPO; JPO;	
		same ridge same (refractive near (index or indice))) and width	DERWENT;	
			IBM_TDB	
-	23	((semiconductor near laser) and (active near (layer or region	USPAT;	2002/05/22 14:31
		or medium or film )) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
		and width) and 372/\$	IBM_TDB	
-	6	((semiconductor near laser) and (active near (layer or region	USPAT;	2004/05/25 10:31
		or medium or film )) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
1		and width) and 257/\$	IBM_TDB	2000 (05 (20 5 4 5 5
-	12	(semiconductor near device) and (active near (layer or region	USPAT;	2002/05/22 14:36
1		or medium or film )) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
1		substrate same ridge same (refractive near (index or indice)))	DERWENT;	
	20	and width	IBM_TDB USPAT;	2002/05/22 14:41
-	30	(semiconductor near (device or laser)) and (active near (layer		2002/05/22 14:41
1	}	or region or medium or film )) and (((dielectric or insulat\$5 or	US-PGPUB;	
		protect\$5) near (film or layer or region or medium)) same	EPO; JPO;	
1		substrate same ridge same (refractive near (index or indice))) and width	DERWENT; IBM_TDB	
	344	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 10:54
1 -	344	(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	2002/03/31 10:34
		insulat\$5) near (film or layer or region or medium)) and ridge	EPO; JPO;	
1		and refractive	DERWENT;	
1		and remactive	IBM_TDB	
1_	114	(semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:23
[ -	114	(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	2002/03/31 13:23
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
1		(ridge or groove) and refractive and (stripe near shaped)	DERWENT;	
1		(11450 of Broove) and remactive and (surperfical snaped)	IBM_TDB	
L	1		101A1 1 0 0	L

-	0	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:33
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)) and	DERWENT;	
		(open\$5 near center) and (open\$5 near rear)	IBM_TDB	
-	108	((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)) and	DERWENT;	
	!	width	IBM_TDB	
-	90	(((semiconductor with optical) and substrate and (active near	USPAT;	2002/05/31 13:38
		(layer or film or region or medium)) and ((protect\$5 or	US-PGPUB;	
		insulat\$5) near (film or layer or region or medium)) and	EPO; JPO;	
		(ridge or groove) and refractive and (stripe near shaped)) and	DERWENT;	
	:	width) and 372/\$	IBM_TDB	
-	27	(semiconductor near laser) and (active near (layer or region or	USPAT;	2002/06/18 11:28
		medium or film )) and (protection near (film or layer or	US-PGPUB;	
	1	region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5)	DERWENT;	
			IBM_TDB	0000 (01/01:01:
+	21	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/04/04 10:46
		medium or film )) and (protection near (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice)) and (open\$5) and (shap\$4)	DERWENT;	
		(UEODO17711   WE177405411   UEOOECOTIN DAT	IBM_TDB	2002 (04 (04 10 40
-	3	("5029175"   "5474954"   "5805627").PN.	USPAT	2003/04/04 10:40
-	23	(semiconductor near laser) and (active near (layer or region or	USPAT; US-PGPUB;	2003/04/04 10:49
		medium or film )) and (protection near (film or layer or	EPO; JPO;	
		region or medium)) and ridge and (refractive near (index or	DERWENT;	
		indice)) and (open\$5) and (shap\$4) and width	IBM_TDB	
	57	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 11:06
-	37	(layer or region or film or medium)) and (protection near	US-PGPUB;	2005/04/04 11:00
		(layer or region or film or medium)) and (ridge or stripe) and	EPO; JPO;	
	1	(refractive near (index or indice)) and width	DERWENT;	
		(Terractive real (mack of make)) and wrath	IBM_TDB	
_	18	(semiconductor near laser) and substrate and (active near	USPAT;	2003/04/04 12:09
		(layer or region or film or medium)) and (protection near	US-PGPUB;	
		(layer or region or film or medium)) and ((ridge or stripe)	EPO; JPO;	
		WITH (refractive near (index or indice))) and width	DERWENT;	
	i		IBM_TDB	
-	14	(semiconductor near laser) and substrate and (protection near	USPAT;	2003/04/04 12:40
		(layer or region or film or medium)) and ((ridge or stripe)	US-PGPUB;	
		WITH (refractive near (index or indice)) WITH (active near	EPO; JPO;	
	1	(layer or region or film or medium))) and width	DERWENT;	
		···	IBM_TDB	
<del>-</del>	405	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/11/13 09:31
	1	medium or film )) and ((protect\$4 or dielectric) near (film or	US-PGPUB;	
	1	layer or region or medium)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))	DERWENT;	
			IBM_TDB	
-	61	(semiconductor near laser) and (active near (layer or region or	USPAT;	2003/11/13 10:34
	1	medium or film )) and (protection near2 (film or layer or	US-PGPUB;	
		region or medium)) and ridge and (refractive near (index or	EPO; JPO;	
		indice))	DERWENT;	
			IBM_TDB	
-	5	(semiconductor near laser) and (active near (layer or region or	USPAT;	2004/05/25 10:31
		medium or film )) and (protection near2 dielectric near2 (film	US-PGPUB;	ļ
		or layer or region or medium)) and ridge and (refractive near	EPO; JPO;	
		(index or indice))	DERWENT;	
1	1		IBM_TDB	